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Supporting Information

Broadband Ultraviolet Plasmonic Enhanced AlGaN/GaN Heterojunction

Photodetectors with Close-packed Al Nanoparticle Array

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Figure S1. Simulated reflectance (a) and transmittance (b) spectra of the AI NPs array on AlGaN/GaN substrate as a function of array period for the particle size of d=40 nm.



Figure S2. Simulated reflectance (a) and transmittance (b) spectra of the AI NPs array on AIGaN/GaN substrate as a function of array period for the particle size of d=100 nm.



Figure S3. AFM images of the AI NPs array (p= 120 nm and d=100 nm) on AlGaN/GaN substrate.(a) Planar view and (b) 3D view of the AI NPs array.



Figure S4. Simulated absorption spectra of the AI NPs array on AIGaN/GaN substrate with different heights of cylinder for the cylinder-ellipsoid composite AI nanoparticle.



Figure S5 Simulated absorption spectra of the AI NPs array on AlGaN/GaN substrate with different heights of AI ellipsoid particle.



Figure S6 Simulated absorption spectra of the AI NPs array on AlGaN/GaN substrate with different surface oxide thicknesses t_{ox} .